

Data Sheet	January 2002	

## 30A, 1000V Ultrafast Diode

The RURP30100 is an ultrafast diode with soft recovery characteristics ( $t_{rr} < 110$ ns). It has a low forward voltage drop and is of silicon nitride passivated, ion-implanted, epitaxial construction.

This device is intended for use as a flywheel/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor.

Formerly developmental type TA09904.

## **Ordering Information**

PART NUMBER	PACKAGE	BRAND
RURP30100	TO-220AC	RUR30100

NOTE: When ordering, use the entire part number.

# Symbol



### **Features**

•	Ultrafast with Soft Recovery<110ns
•	Operating Temperature175°C
•	Reverse Voltage
	A

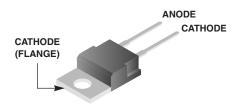
- · Avalanche Energy Rated
- Planar Construction

# **Applications**

- · Switching Power Supply
- · Power Switching Circuits
- General Purpose

# **Packaging**

**JEDEC TO-220AC** 



<b>Absolute Maximum Ratings</b> T <sub>C</sub> = 25°C, Unless Otherwise Specified		
Abbolate maximum ridings 16 = 25 0, onless outlowise opening	RURP30100	UNITS
Peak Repetitive Reverse Voltage	1000	V
Working Peak Reverse Voltage	1000	V
DC Blocking VoltageV <sub>R</sub>	1000	V
Average Rectified Forward Current $I_{F(AV)}$ ( $T_C = 120^{\circ}C$ )	30	Α
Repetitive Peak Surge Current	60	Α
Nonrepetitive Peak Surge Current	300	Α
Maximum Power Dissipation	125	W
Avalanche Energy (See Figures 7 and 8)	30	mJ
Operating and Storage Temperature	-65 to 175	°С

**Electrical Specifications**  $T_C = 25^{\circ}C$ , Unless Otherwise Specified.

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> = 30A	-	-	1.8	V
	$I_F = 30A, T_C = 150^{\circ}C$	-	-	1.6	V
I <sub>R</sub>	V <sub>R</sub> = 1000V	-	-	250	μΑ
	$V_R = 1000V, T_C = 150^{\circ}C$	-	-	1	mA
t <sub>rr</sub>	$I_F = 1A$ , $dI_F/dt = 100A/\mu s$	-	-	110	ns
	$I_F = 30A$ , $dI_F/dt = 100A/\mu s$	-	-	150	ns
t <sub>a</sub>	$I_F = 30A$ , $dI_F/dt = 100A/\mu s$	-	90	-	ns
t <sub>b</sub>	$I_F = 30A$ , $dI_F/dt = 100A/\mu s$	-	45	-	ns
$R_{ heta JC}$		-	-	1.2	°C/W

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

 $t_{rr}$  = Reverse recovery time at  $dI_F/dt$  = 100A/ $\mu$ s (See Figure 6), summation of  $t_a + t_b$ .

 $t_a$  = Time to reach peak reverse current at  $dI_F/dt$  = 100A/ $\mu$ s (See Figure 6).

t<sub>b</sub> = Time from peak I<sub>RM</sub> to projected zero crossing of I<sub>RM</sub> based on a straight line from peak I<sub>RM</sub> through 25% of I<sub>RM</sub> (See Figure 6).

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

# Typical Performance Curves

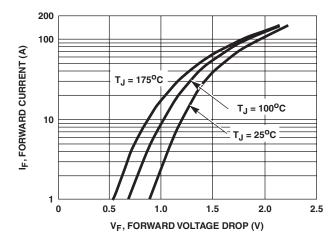


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

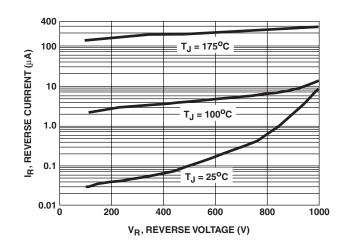


FIGURE 2. REVERSE VOLTAGE vs REVERSE CURRENT

# Typical Performance Curves (Continued)

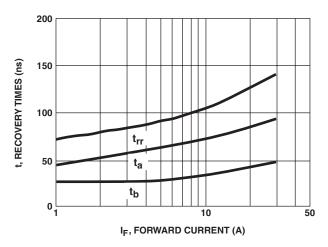


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

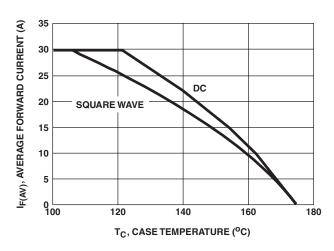
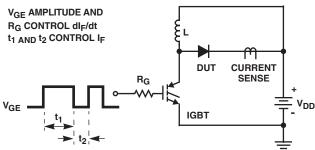
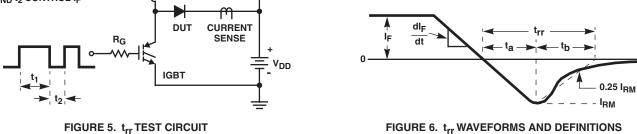


FIGURE 4. CURRENT DERATING CURVE

### Test Circuits and Waveforms





I = 1.225A L = 40mH  $R < 0.1\Omega$  $E_{AVL} = \frac{1}{2}LI^{2} \left[ V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]$ Q1 = IGBT (BVCES > DUT VR(AVL)) CURRENT  $V_{DD}$ SENSE  $V_{DD}$ DUT

FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

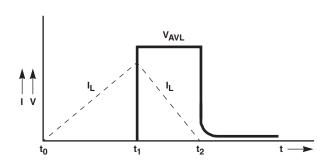


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE **WAVEFORMS** 

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

SMART START™  $VCX^{TM}$ FAST ® OPTOLOGIC™ STAR\*POWER™ FASTr™ Bottomless™ OPTOPLANAR™ Stealth™ CoolFET™ FRFET™ PACMAN™ SuperSOT™-3 CROSSVOLT™ GlobalOptoisolator™ POP™ SuperSOT™-6 DenseTrench™ GTO™ Power247™ SuperSOT™-8 HiSeC™ PowerTrench® DOME™ SyncFET™ EcoSPARK™ ISOPLANAR™ QFET™ TinyLogic™ E<sup>2</sup>CMOS<sup>TM</sup> LittleFET™  $OS^{TM}$ 

EnSigna™ MicroFET™ QT Optoelectronics™ TruTranslation™
FACT™ MicroPak™ Quiet Series™ UHC™
FACT Quiet Series™ MICROWIRE™ SILENT SWITCHER® UltraFET®

STAR\*POWER is used under license

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. H4